

Low temperature sintering of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics using $\text{B}_2\text{O}_3/\text{CuO}$ and $\text{BaCu}(\text{B}_2\text{O}_5)$ additives

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Abstract

The effects of $\text{B}_2\text{O}_3/\text{CuO}$ and $\text{BaCu}(\text{B}_2\text{O}_5)$ additives on the sintering temperature and microwave dielectric properties of $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics were investigated. The B_2O_3 added $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics were not able to be sintered below 1000 °C. However, when both CuO and B_2O_3 were added, they were sintered below 900 °C and had the good microwave dielectric properties. It was suggested that a liquid phase with the composition of $\text{BaCu}(\text{B}_2\text{O}_5)$ was formed during the sintering and assisted the densification of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics at low temperature. $\text{BaCu}(\text{B}_2\text{O}_5)$ powders were produced and used to reduce the sintering temperature of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics. Good microwave dielectric properties of $Q_{\text{xf}} = 16,000$ GHz, $\epsilon_r = 36.0$ and $\tau_f = 9.11$ ppm/°C were obtained for the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics containing 10.0 mol% $\text{BaCu}(\text{B}_2\text{O}_5)$ sintered at 875 °C for 2 h.

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1. Introduction

Recently, low temperature co-fired ceramic (LTCC) multilayer devices, composed of alternating dielectric ceramics and internal metallic electrode layers, have been extensively investigated for the miniaturization of microwave dielectric components.^{1,2} LTCC multilayer devices consist of alternating microwave dielectric ceramics and internal metallic electrode layers.¹ Ag has been widely used as the metallic electrode, because of its high conductivity and low cost. However, the melting temperature of Ag is low, about 961 °C, whereas the sintering temperature of the microwave dielectric ceramics is generally above 1400 °C. Therefore, for the fabrication of multilayer devices, it is necessary to develop microwave dielectric ceramics with a low sintering temperature, which can be co-fired with Ag.

The BaO-TiO_2 system has been extensively studied and a number of researchers have reported on this system, which has many compounds and excellent microwave dielectric properties.^{3–5} In particular, the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ microwave dielectric

ceramics, which were reported by Jonker and Kwestroo, exhibited good microwave dielectric properties with a high dielectric constant (ϵ_r) of 39.8, a high Q -factor of 8000 at 4 GHz and near zero temperature coefficient of resonance frequency (τ_f).^{5,6} However, since the sintering temperature of these $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics is high, they can not be used as LTCC and, consequently, many attempts have been made to lower their sintering temperature. $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics containing 1.0 wt.% $3\text{ZnO-B}_2\text{O}_3$ were sintered at 940 °C, but their microwave dielectric properties were low.⁷ BaBSiO glass was also used to reduce the sintering temperature of $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics and this enabled their sintering temperature to be reduced to 900 °C, but they exhibited very low microwave dielectric properties of $Q_{\text{xf}} = 1150$ GHz, and $\epsilon_r = 13.2$.⁸ $\text{PbO-B}_2\text{O}_3\text{-SiO}_2$ and $\text{MgO-CaO-SiO}_2\text{-Al}_2\text{O}_3$ glasses were also used to reduce the sintering temperature of $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics, but the results were not satisfactory.^{9,10} In previous studies, the addition of a small amount of B_2O_3 and CuO was found to reduce the sintering temperature of BaTi_4O_9 ceramics to below 900 °C and a liquid phase with the composition of $\text{BaCu}(\text{B}_2\text{O}_5)$ was thought to assist in their densification.¹¹ Moreover, BaTi_4O_9 ceramics containing $\text{BaCu}(\text{B}_2\text{O}_5)$ sintered below 900 °C without deteriorating their good microwave dielectric properties.¹² Therefore, it is also possible that these $\text{B}_2\text{O}_3/\text{CuO}$

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and $\text{BaCu}(\text{B}_2\text{O}_5)$ additives would be effective in decreasing the sintering temperature of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics. In this work, these additives were used to reduce the sintering temperature of $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics and their effects on the microwave dielectric properties were also investigated.

2. Experimental procedure

To prepare the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics, BaCO_3 (High Purity Chemicals, >99%, Japan) and TiO_2 (High Purity Chemicals, >99%, Japan) were mixed in a nylon jar with zirconia balls for 24 h, and then dried and calcined at 1180°C for 6 h. After remilling with the B_2O_3 (High Purity Chemicals, >99%, Japan) and CuO (High Purity Chemicals, >99%, Japan) and $\text{BaCu}(\text{B}_2\text{O}_5)$ additives, the powder was dried, pressed into discs and sintered at 875 – 1000°C for 2 h. For the $\text{BaCu}(\text{B}_2\text{O}_5)$, oxide compounds of BaO (High Purity Chemicals, >99%, Japan), CuO (High Purity Chemicals, >99%, Japan) and B_2O_3 (High Purity Chemicals, >99%, Japan) were mixed in a nylon jar with zirconia balls for 24 h, and then dried and calcined at 700°C for 3 h. The microstructure of the specimens was studied using X-ray diffraction (Rigaku D/max-RC, Japan), and scanning electron microscopy (SEM: Hitach S-4300, Japan). The densities of the sintered specimens were measured by a water-immersion technique. The dielectric properties in the microwave frequency range were measured by a dielectric post resonator technique suggested by Hakki and Coleman and Courtney.^{13,14} The temperature coefficients of the resonant frequency was measured at 6.5 GHz in the temperature range of 25 – 90°C .

3. Results and discussion

Fig. 1(a) shows the XRD pattern of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ powders calcined at 1180°C for 6 h. Most of the peaks were indexed as those of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$. Peaks for the BaTi_4O_9 and $\text{Ba}_4\text{Ti}_{13}\text{O}_{30}$ second phases were also observed in this specimen. Fig. 1(b)–(e) show the XRD patterns of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics containing x mol% of B_2O_3 with $2.0 \leq x \leq 20.0$ sintered at 1000°C for 2 h. When B_2O_3 was added to the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics, their

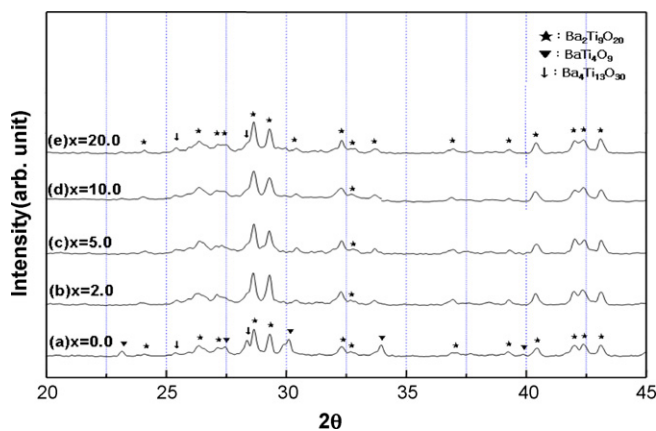


Fig. 1. (a) XRD pattern of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ powders calcined at 1180°C and XRD patterns of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics containing x mol% of B_2O_3 with (b) $x = 2.0$; (c) $x = 5.0$; (d) $x = 10.0$; $x = 20.0$ sintered at 1000°C for 2 h.

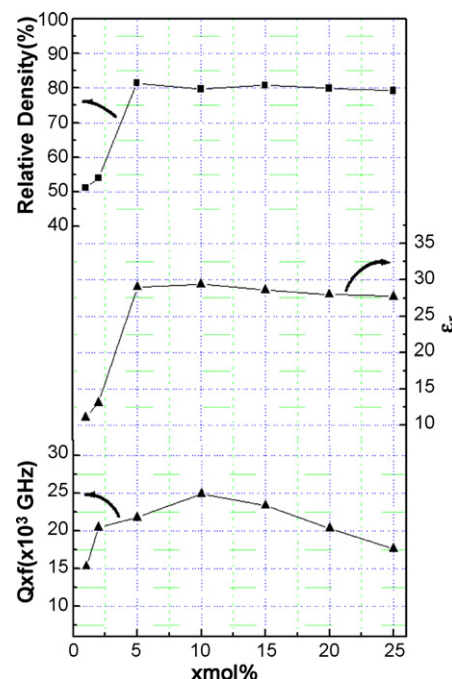


Fig. 2. Variations of the relative density, ϵ_r and Qxf value of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics containing x mol% of B_2O_3 with $1.0 \leq x \leq 25.0$ sintered at 1000°C for 2 h.

sintering temperature was reduced to 1000°C and the amount of BaTi_4O_9 and $\text{Ba}_4\text{Ti}_{13}\text{O}_{30}$ second phases decreased. Previously, it was suggested that the sintering of the 5.0 wt.% B_2O_3 added $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics was assisted by the presence of a liquid.¹⁵ Furthermore, for the B_2O_3 added BaTi_4O_9 ceramics, a liquid phase containing BaO and B_2O_3 was formed during the sintering and assisted in the densification of the BaTi_4O_9 ceramics at 875°C .¹¹ For the B_2O_3 added $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics, peaks for the BaO – B_2O_3 second phase were not found. However, since the amounts of the BaTi_4O_9 and $\text{Ba}_4\text{Ti}_{13}\text{O}_{30}$ second phases decreased with the addition of B_2O_3 , it is considered that some of the BaO in these second phases reacted with B_2O_3 , resulting in the formation of BaO – B_2O_3 liquid phase, which assisted the densification of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ at 1000°C . Furthermore, these second phases changed into the Ti-rich phase, i.e. $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ phase, after reacting with B_2O_3 .

Fig. 2 shows the variations of the relative density, ϵ_r and Qxf value of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics containing x mol% of B_2O_3 with $1.0 \leq x \leq 25.0$ sintered at 1000°C for 2 h. The relative density of the specimen with 2.0 mol% of B_2O_3 was very low, being approximately 55% of the theoretical density, and increased with increasing B_2O_3 content to reach a saturated value when 5.0 mol% of B_2O_3 was added. The variation of ϵ_r is similar to that of the relative density. The Q -value increased with the addition of B_2O_3 due to the increase in the density and reached a maximum value of 25000 GHz for the specimen containing 10.0 mol% of B_2O_3 . However, it decreased when the B_2O_3 content was further increased and this decrease was attributed to the increase in the amount of the liquid phase. The B_2O_3 added $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics were not able to be sintered below 1000°C and, thus, it would be difficult to use Ag as the

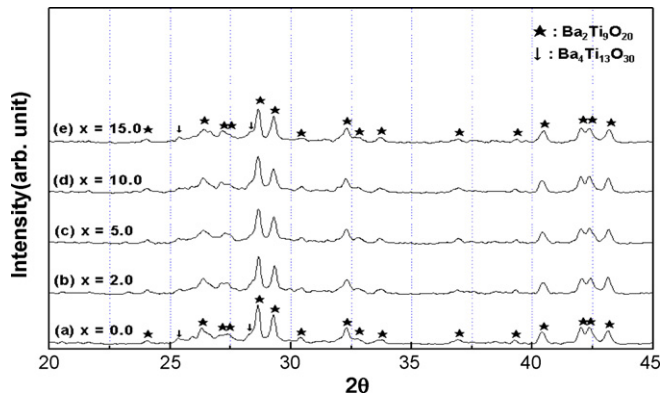


Fig. 3. XRD patterns of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics containing 10.0 mol% of B_2O_3 and x mol% of CuO with (a) $x=0.0$; (b) $x=2.0$; (c) $x=5.0$; (d) $x=10.0$; (e) $x=20.0$ sintered at 900°C for 2 h.

electrode for them. Therefore, both CuO and B_2O_3 were added to the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics in an attempt to reduce the sintering temperature below 950°C .

When CuO was added to the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics containing 10.0 mol% B_2O_3 , they were able to be sintered at temperatures as low as 875°C . Fig. 3 shows the X-ray diffraction patterns of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics containing 10.0 mol% of B_2O_3 and x mol% of CuO with $0.0 \leq x \leq 15.0$ sintered at 900°C for 2 h. Most of the peaks were indexed as those of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ phase and peaks for the $\text{Ba}_4\text{Ti}_{13}\text{O}_{30}$ second phase indicated by an arrow were also observed. No variation of the XRD pattern was observed with the addition of CuO . The CuO additive itself cannot be responsible for reducing the sintering temperature of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics below 900°C , because the CuO added $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics were not sintered below 1060°C . According to a previous work, $\text{BaCu}(\text{B}_2\text{O}_5)$ second phase was observed in the CuO and B_2O_3 added $\text{Ba}(\text{Zn}_{1/3}\text{Nb}_{2/3})\text{O}_3$ ceramics and assisted in the densifi-

cation of the specimens at low temperature.¹⁶ In the case of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics, however, it was difficult to identify the presence of the $\text{BaCu}(\text{B}_2\text{O}_5)$ second phase using XRD pattern. A similar result was also observed for the CuO and B_2O_3 added BaTi_4O_9 ceramics.¹¹ On the other hand, the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics were well sintered even at 875°C when a small amount of $\text{BaCu}(\text{B}_2\text{O}_5)$ was added, as will be discussed later. Therefore, it is considered that the liquid phase with the composition of $\text{BaCu}(\text{B}_2\text{O}_5)$ might be responsible for the densification of the CuO and B_2O_3 added $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics at low temperature. Furthermore, it is thought that $\text{BaCu}(\text{B}_2\text{O}_5)$ second phase existed as an amorphous phase in $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics after cooling.

Fig. 4(a)–(c) show the SEM images of the thermally etched surfaces of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics containing 10.0 mol% of B_2O_3 and x mol% of CuO with $2.0 \leq x \leq 15.0$ sintered at 900°C for 2 h. For the specimen containing 2.0 mol% of CuO , a porous microstructure was formed. However, when 10.0 mol% CuO was added, a dense microstructure developed. Therefore, densification occurred when x exceeded 10.0 mol%.

Fig. 5 shows the variations in the relative density and ε_r value of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics containing 10.0 mol% of B_2O_3 and x mol% of CuO with $2.0 \leq x \leq 15.0$ sintered at 900°C . The relative density of the specimens was low when a small amount of CuO was added, but it considerably increased when x exceeded 5.0 mol%. The variation in the relative density is closely related to the microstructure, as shown in Fig. 4(a)–(c). A similar result was also obtained for the specimens sintered at 875°C , although the relative density of all these specimens is low. The variation in ε_r is similar to that of the density and a saturated ε_r value of 33.6 was obtained for the specimens with 10.0 mol% of CuO . Thus, it can be inferred that the density is the important factor contributing to the improvement of the ε_r value of the specimen. The Q -value of the specimens increased with the addition of CuO and

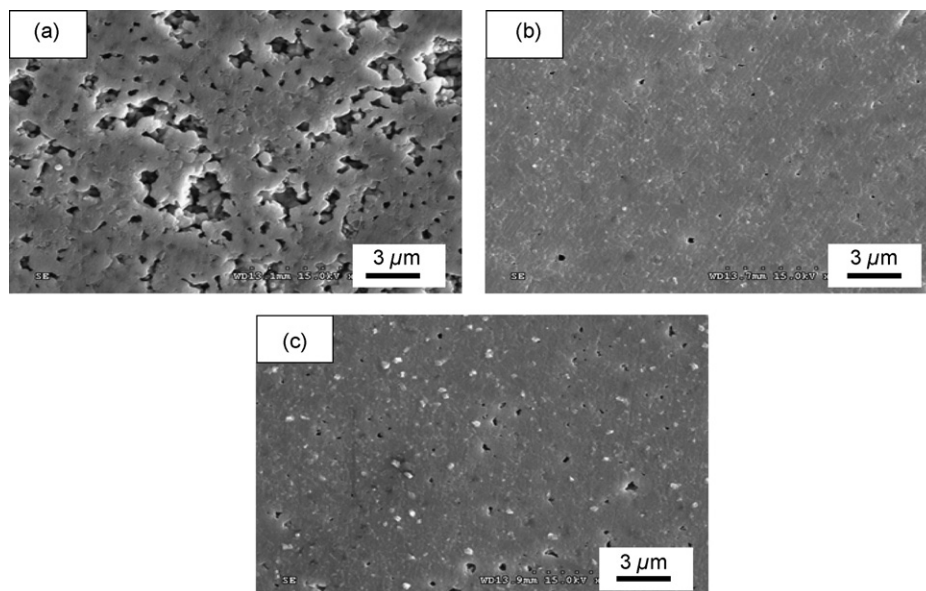


Fig. 4. SEM images of the thermally etched surfaces of the $\text{Ba}_2\text{Ti}_9\text{O}_{20}$ ceramics containing 10.0 mol% of B_2O_3 and x mol% of CuO with (a) $x=2.0$; (b) $x=10.0$; (c) $x=15.0$ sintered at 900°C for 2 h.

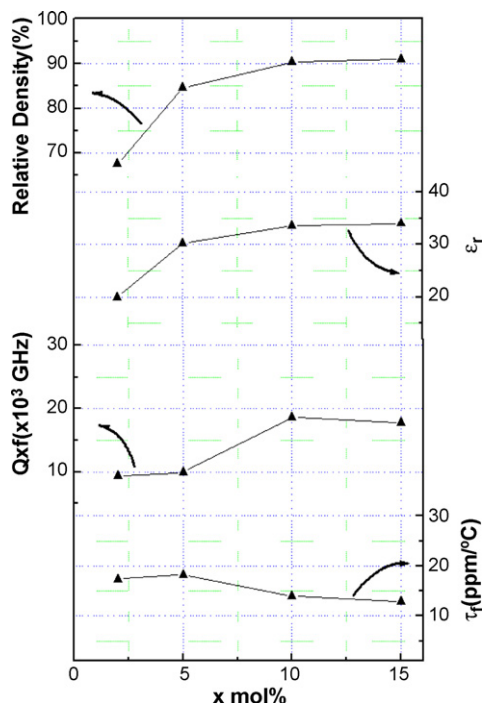


Fig. 5. Variations in the relative density, ϵ_r , Qxf value and τ_f of the Ba₂Ti₉O₂₀ ceramics containing 10.0 mol% of B₂O₃ and x mol% of CuO with $2.0 \leq x \leq 15.0$ sintered at 900 °C for 2 h.

showed a maximum value of 18,600 GHz when $x = 10.0$ mol%, as shown in Fig. 5. The increase in the Q -value is attributed to the increase in the density. The τ_f of specimens ranged between 12.9 and 18.3 ppm/°C and did not change with the addition of CuO. Therefore, the Ba₂Ti₉O₂₀ ceramics containing 10.0 mol% B₂O₃ and 10.0 mol% CuO sintered at 900 °C exhibited good microwave dielectric properties of $\epsilon_r = 33.6$, Qxf = 18,600 GHz and $\tau_f = 14.0$ ppm/°C.

To clarify the effect of the BaCu(B₂O₅) phase on the sintering temperature and microwave dielectric properties of the Ba₂Ti₉O₂₀ ceramics, BaCu(B₂O₅) powders were synthesized and added to the Ba₂Ti₉O₂₀ ceramics. Fig. 6 shows the variations of the relative density, ϵ_r , Qxf value and τ_f of the Ba₂Ti₉O₂₀ + x BaCu(B₂O₅) ceramics with $5.0 \leq x \leq 20.0$ mol% sintered at 875 °C for 2 h. The relative density was low for the specimen containing 5.0 mol% of BaCu(B₂O₅) and increased with increasing BaCu(B₂O₅) content. The variation of ϵ_r is similar to that of the relative density and a saturated ϵ_r value of 36.0 was obtained for the specimen with $x = 10.0$ mol%. The Qxf value also increased with the addition of BaCu(B₂O₅), because of the increased density. However, it slightly decreased when x exceeded 15.0 mol% and this decrease can be explained by the formation of a large amount of liquid phase. A maximum Qxf value of 16,000 GHz was obtained when $x = 10.0$ mol%. The variation of τ_f with the addition of BaCu(B₂O₅) was not significant, with its value ranging between 9.11 and 10.30 ppm/°C, as shown in Fig. 6. Good microwave dielectric properties of Qxf = 16,000 GHz, $\epsilon_r = 36.0$ and $\tau_f = 9.11$ ppm/°C were obtained for the Ba₂Ti₉O₂₀ + 10.0 mol% BaCu(B₂O₅) ceramics sintered at 875 °C for 2 h. These results are similar to

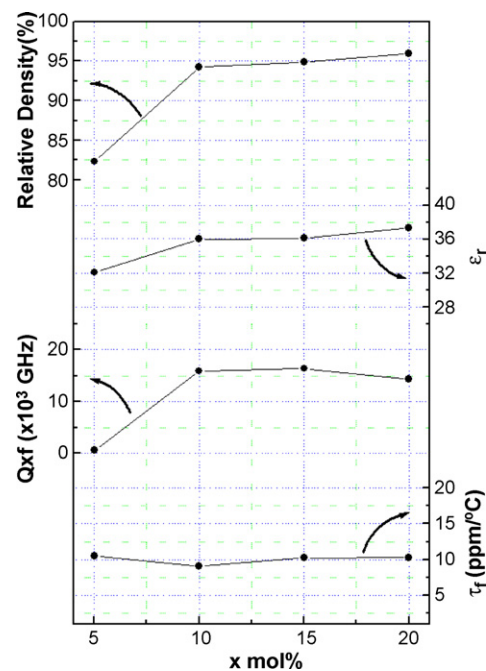


Fig. 6. Variations of the relative density, ϵ_r , Qxf value and τ_f of the Ba₂Ti₉O₂₀ + x BaCu(B₂O₅) ceramics with $5.0 \leq x \leq 20.0$ mol% sintered at 875 °C for 2 h.

those of B₂O₃ and CuO added Ba₂Ti₉O₂₀ ceramics. Therefore, it can be inferred that BaCu(B₂O₅) second phase was formed in the B₂O₃ and CuO added Ba₂Ti₉O₂₀ ceramics and helped in their densification at low temperature. Moreover, it can be concluded that the BaCu(B₂O₅) phase constitutes a good additive for decreasing the sintering temperature of Ba₂Ti₉O₂₀ ceramics.

4. Conclusions

The sintering temperature of Ba₂Ti₉O₂₀ ceramics is near 1300 °C but it was reduced to 1000 °C when B₂O₃ was added. BaTi₄O₉ and Ba₄Ti₁₃O₃₀ second phases reacted with the B₂O₃ forming a liquid phase containing BaO and B₂O₃ which assisted in the densification of the Ba₂Ti₉O₂₀ ceramics at low temperature. The B₂O₃ added Ba₂Ti₉O₂₀ ceramics were not able to be sintered below 1000 °C, but the Ba₂Ti₉O₂₀ ceramics containing both CuO and B₂O₃ were sintered at 900 °C. It was suggested that BaCu(B₂O₅) liquid phase was responsible for the densification of the CuO and B₂O₃ added Ba₂Ti₉O₂₀ ceramics at low temperature. BaCu(B₂O₅) was also added Ba₂Ti₉O₂₀ in order to reduce its sintering temperature. Good microwave dielectric properties of Qxf = 16,000 GHz, $\epsilon_r = 36.0$ and $\tau_f = 9.11$ ppm/°C were obtained for the Ba₂Ti₉O₂₀ ceramics containing 10.0 mol% BaCu(B₂O₅) sintered at 875 °C for 2 h.

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